

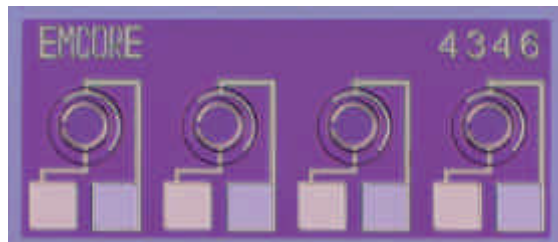
1 x 4 GaAs PIN Photodiode Array

Product Description

EMCORE's 4 channel Gallium Arsenide (GaAs) PIN photodiode array is designed for multimode fiber applications. Utilizing EMCORE's own state-of-the-art MOCVD wafer foundry and device fabrication facility guarantees a reliable high volume fabrication source of package ready die to meet the growing needs of fiber optic component manufacturers. Excellent device performance and robust operation makes the 8485-1400 the superior device for multimode optical communication applications.

Features

- Data rates of 3.125 Gb/s per channel
- Excellent responsivity
- Uniform channel to channel characteristics
- Excellent crosstalk attenuation
- Low dark current



P contact

Product Specifications

Electro-Optical Characteristics (T = 30°C)

	Conditions	Min.	Typical	Max.	Unit
Speed		4	5		GHz
Responsivity	3 to -26 dBm, 850 nm Epoxy coated, n=1.6	.4	.5		A/W
Response Variation	3 to -26 dBm, 850 nm		2	3	%
Active Area (aperture)	-		70		μm
Crosstalk Attenuation	3 dBm, -1.6 V	30	40		dB
Rise/Fall Time	-1.6 V bias		32/75	50/100	ps
Dark Current	-1.6 V, -70 dBm		.5	3	nA
Capacitance	-1.6 V, 1 MHz	.35	.4	.5	pF
Reverse Breakdown	1 μA	20	50		V
Reflectivity	Epoxy coated, n=1.6			1	%

Physical Description

	Min.	Typical	Max.	Unit
Die Length	1035	1055	1075	μm
Die Width	430	450	470	μm
Die Height	180	200*	220	μm
Diode Pitch		250		μm
Bond Pads		80x80		μm
Substrate		Semi-Insulating GaAs		

* Use P/N 8485-1401 for 625 um height.

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